

AMENDMENTS TO THE SPECIFICATION

Please insert the paragraph on page 1, before line 4, as follows:

This is a continuation of U.S. Patent Application Serial No. 10/182,835, which is the national phase of PCT/JP01/10590, filed December 4, 2001.

Please amend the paragraph on page 127, line 9, to line 20, as follows:

A first plating process is performed by immersing the semiconductor substrate W into a first plating liquid, such as a high throwing power copper sulfate plating liquid used for printed circuit boards. This process forms a uniform initial thin plated film over the entire surface of the trenches formed in the surface of the semiconductor substrate W, wherein the surface includes the bottom and side walls of the trenches. Here, the high throwing power copper sulfate solution has a low concentration of copper sulfate, a high concentration of sulfuric acid, and is superior in throwing power and coating uniformity. An example composition of this solution is 5_100 g/l of copper sulfate and 100_250 g/l of sulfuric acid.

Please amend the paragraph on page 127, line 28, to page 128, line 4, as follows:

After washing the semiconductor substrate W, a second plating process is performed by immersing the semiconductor substrate W into a second plating liquid, such as a copper sulfate plating liquid for decorative uses. This process fills copper into the trenches and forms a plated film having a flat surface on the surface of the substrate. Here, the copper sulfate plating liquid has a high concentration of copper sulfate and a low concentration of sulfuric acid and is superior in leveling ability. An example composition of the solution is 100_300 g/l of copper sulfate and 10_100 g/l of sulfuric acid.